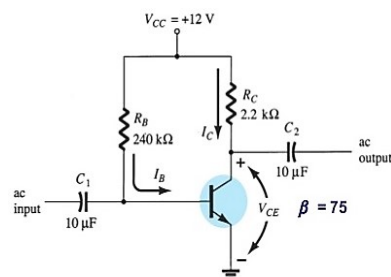


## Sample Questions

- 1) Why collector is made larger than emitter and base?
- 2) Different between CE, CB, and CC configuration in BJT.
- 3) Why CE configuration is most popular in amplifier circuits?
- 4) In the fixed bias circuit of a transistor,  $V_{CC} = 12\text{ V}$ ,  $R_B = 240\text{ K}\Omega$  and  $R_C = 2.2\text{ K}\Omega$ . If  $\beta = 50$  and  $V_{BE} = 0.7\text{ V}$ . Determine  $I_B$ ,  $I_C$ ,  $V_{CE}$ ,  $V_{BC}$ .
- 5) What is early effect or base width modulation in BJT?
- 6) For a BJT, CB current gain is 0.965,  $I_{CBO} = 0.85\text{ }\mu\text{A}$ . This BJT is now connected in CE mode and operated in active region with a base current of  $30\text{ }\mu\text{A}$ . Then find the value of collector current.
- 7) What is the significance of load line and Q-point in BJT? What is the best position of Q point for amplification?
- 8) Biasing is required for Bipolar Junction Transistor (BJT) amplifier. Justify.
- 9) The base and collector current are  $100\text{ }\mu\text{A}$ ,  $2.9\text{ mA}$  respectively for BJT in common emitter configuration. Evaluate the value of current gain  $\alpha$  and  $\beta$ . Neglect the leakage current for the transistor.
- 10) Determine the transistor node voltages and current label in the given bias arrangement. Assume the transistor is of Silicon.

- |                     |               |
|---------------------|---------------|
| (i) $I_B$ and $I_C$ | (ii) $V_{CE}$ |
| (iii) $V_B$         | (iv) $V_C$    |

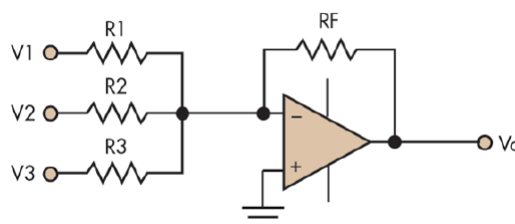


- 11) Draw both the I-V characteristics for NPN transistor in CE configuration. Show different region of operation with proper labeling of  $V_{CESat}$ ,  $V_{CEmax}$ ,  $I_{CEO}$ ,  $I_{CSat}$  and dc load line. Discuss about the Q-point and its relevance towards amplifier design.
- 12) Draw a neat diagram to show the current components for a p-n-p bipolar junction transistor (BJT).
- 13) Explain the input and output characteristics of a silicon transistor in CB configuration with suitable circuit diagram.
- 14) If value of  $\beta$  is 150, find out value of  $\alpha$ .
- 15) Determine the operating point for a silicon transistor biased by base bias method with  $\beta = 100$ ,  $R_B = 500\text{ K}\Omega$ ,  $R_C = 2.5\text{ K}\Omega$  and  $V_{CC} = 20\text{ V}$ . Also draw the DC load line.
- 16) For a CE configuration of NPN transistor, if the base current is  $80\text{ }\mu\text{A}$  and emitter current is  $1.2\text{ mA}$ . Calculate the value of  $\alpha$  and  $\beta$ .
- 17) What is a transistor? Write different types of transistor with symbols.
- 18) Explain the working of npn and pnp transistor.
- 19) Explain how transistor acts as an amplifier.

## Sample Questions

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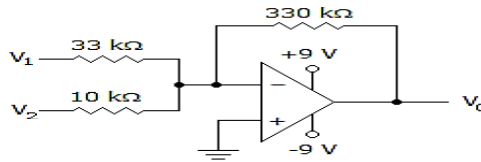
- 20) Define the terminals of transistor.
- 21) What are the different types of transistor configuration?
- 22) Draw and explain common emitter configuration. Also write the expression for output current.
- 23) Write the relationship between  $\alpha$ ,  $\beta$  and  $\gamma$ .
- 24) Draw the input and output characteristics curve of CB configuration.
- 25) Draw the input and output characteristics curve of CE configuration.
- 26) What is Faithful amplification?
- 27) What is biasing? Why we need biasing?
- 28) State the difference between CB, CE and CC.
- 29) Explain Fixed biasing with neat diagram.
- 30) Explain dc load line.
- 31) What is Q-point? What is the significance of Q-point?
- 32) The base and collector current are  $100\text{ }\mu\text{A}$ ,  $2.9\text{ mA}$  respectively for BJT in common emitter configuration. Find the value of current gain  $\alpha$  and  $\beta$
- 33) Si n-p-n transistor with  $\beta=100$  and  $I_{CBO}=20\mu\text{A}$  is connected in CE mode. Find the collector current for a base current of  $0.02\text{mA}$
- 34) For a BJT, CB current gain is  $0.96$ ,  $I_{CBO}=0.8\text{ }\mu\text{A}$ . This BJT is now connected in CE mode and operated in active region with a base current of  $40\text{ }\mu\text{A}$ . Then find the value of collector current.
- 35) Solve to find  $I_B$ ,  $I_C$ ,  $V_{CE}$  and  $V_C$  for a fixed bias BJT circuit of a Si transistor,  $V_{CC} = 10\text{ V}$ ,  $R_B = 100\text{ K}\Omega$  and  $R_C = 2\text{ K}\Omega$  and  $\beta = 100$ .
- 36) Write down any four properties of a practical op-amp.
- 37) Draw the circuit diagram of integrator and differentiator amplifier using OP-AMP and derive their output voltage expression.
- 38) A differential dc amplifier has a differential mode gain of  $100$  and a common mode gain of  $0.01$ . What is its CMRR in dB?
- 39) For an Op-Amp differential mode gain is  $1000$  and common mode gain is  $10$ , find CMRR in dB ?
- 40) Find the output voltage  $V_0$  of the following circuit. Given  $R_1=1\text{k}\Omega$ ,  $R_2=1\text{k}\Omega$ ,  $R_3=1\text{k}\Omega$ ,  $R_F=4\text{k}\Omega$ ,  $V_1=2\text{ V}$ ,  $V_2=3\text{ V}$  and  $V_3=5\text{ V}$ . The OPAMP is biased with  $+12\text{V}$  DC power supply.



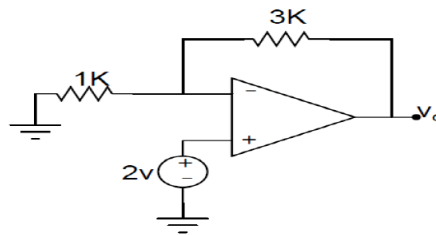
- 41) Why OPAMP is preferred to be operated as negative feedback configuration?

## Sample Questions

- 42) Draw an inverting and non-inverting amplifier configuration using OPAMP and derive its output voltage.
- 43) Determine the output voltage when  $V_1 = -V_2 = 1\text{ V}$  for the given OPAMP configuration.



- 44) Find the output voltage  $V_o$  ?



- 45) Draw the circuit diagram of Summing and Differential Amplifier using op-amp & derive their output voltage expression.
- 46) Differentiate between JFET and BJT .
- 47) Draw and explain the physical structure, drain characteristics and symbolic representation of a n-channel JFET.
- 48) Draw the physical structure, circuit symbol, drain characteristics and transfer characteristics of a n-channel E-MOSFET. Briefly explain, that how this is different from D-MOSFET?
- 49) Draw the physical structure, drain characteristics, transfer characteristics and symbol of a n-channel depletion type MOSFET.
- 50) Find Drain current of a n-channel D-MOSFET. If  $I_{DSS} = 10\text{ mA}$  &  $V_p = -6\text{ V}$ ,  $V_{GS} = -2\text{ V}$ .
- 51) What is MOSFET and write down two advantages?
- 52) Draw the physical structure, drain characteristics, transfer characteristics and circuit symbol of a P-channel D-MOSFET.
- 53) What is the main difference between depletion and enhancement type MOSFET?
- 54) Draw the transfer characteristics of an EMOSFET.
- 55) Write down Shockley's equation for drain current of a FET and interpret all the notations.
- 56) Why FET is called as Unipolar and Voltage controlled device.
- 57) Define the parameters ( $g_m$ ,  $\mu$ ,  $r_d$ ) of JFET and find the relationship between them.
- 58) Write down three advantages for which MOSFET is used in VLSI circuits.
- 59) Name any four factors which make the JFET superior to BJT.
- 60) Define threshold voltage of EMOSFET.

## Sample Questions

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- 61) How the pinch-off condition is achieved in JFET?
- 62) Analyze the CMOS as an inverter. Draw and identify different regions of the output Characteristic of JFET.
- 63) Design a CMOS inverter circuit and explain its operation.
- 64) What happens when diode is zero biased, forward biased and reverse biased?
- 65) Write the diode equation and draw the VI characteristics of diode.
- 66) Why Si and Ge are commonly used semiconductor.
- 67) Write the applications of diode.
- 68) Explain filter circuit. Write different types of filter circuit.
- 69) Explain center tapped full wave rectifier with its output waveform.
- 70) Calculate the efficiency of half wave Rectifier and full wave rectifier.
- 71) What is ripple? Calculate the ripple factor of half wave and full wave rectifier.
- 72) State the difference between avalanche and zener breakdown.
- 73) Explain how Zener diode acts as a voltage regulator.
- 74) Draw the VI characteristics of Zener diode.
- 75) Calculate the PIV of half wave, centre tapped rectifier.
- 76) Explain bridge rectifier with its output waveform.
- 77) Explain the simplified, ideal and equivalent model of diode with its V-I characteristics curve.
- 78) Explain Semiconductor with its energy band diagram.
- 79) State the difference between diode and Zener diode.
- 80) Define doping, diffusion, knee voltage, PIV, and maximum forward current.
- 81) What is reverse saturation current, drift current, diffusion current.
- 82) What is effect of adding a capacitor across the load in a rectifier circuit? Explain with diagram.
- 83) Define static and dynamic resistance of P-N diode.
- 84) What is the effect of temperature on the conductivity of semiconductor?
- 85) Write the difference between half wave and centre tap full wave rectifier in terms of efficiency, ripple factor and PIV.
- 86) A centre tap full wave rectifier uses two diodes with an equivalent forward resistance  $50\Omega$ . If the input a.c voltage is  $50 \sin(200\pi t)V$  and the load resistance of  $950\Omega$ . Calculate
  - i) Peak, average and r.m.s value of current
  - ii) Efficiency
  - iii) Ripple factor
- 87) Define modulation? What are the types of analog modulation?
- 88) What is the need for modulation?
- 89) What is the difference between amplitude modulation and frequency modulation?
- 90) Describe the function of core and cladding in optical fiber.

## Sample Questions

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- 91) What is acceptance angle? Why do we need to know this angle?
- 92) Why is it necessary to meet the total reflection requirement inside an optical fiber?
- 93) What is meant by the term critical propagation angle?
- 94) What are the advantages and disadvantages of fiber optic communications?
- 95) State Snell's Law.
- 96) Difference in LED and Laser.